

New Jersey Semi-Conductor Products, Inc.

20 STERN AVE.
SPRINGFIELD, NEW JERSEY 07081
U.S.A.

TELEPHONE: (973) 376-2922
(212) 227-6005
FAX: (973) 376-8960

BUV50

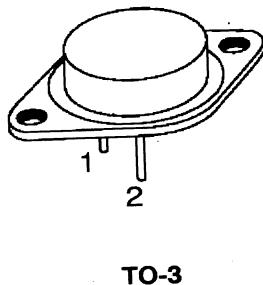
High Power NPN Silicon Transistor

Application

Switching regulators
Motor control

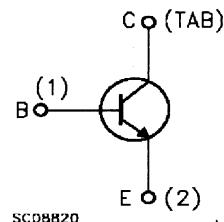
Description

NPN transistor
High current capability
Fast switching speed
Fully characterized



TO-3

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CEV}	Collector-Emitter Voltage ($V_{BE} = -1.5V$)	250	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	125	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	7	V
I_C	Collector Current	25	A
I_{CM}	Collector Peak Current	50	A
I_B	Base Current	6	A
I_{BM}	Base Peak Current	12	A
P_{Base}	Reverse Bias Base Power Dissipation (B.E. junction in avalanche)	2	W
P_{tot}	Total Power Dissipation at $T_{case} \leq 25^\circ C$	150	W
T_{stg}	Storage Temperature	-65 to 200	°C
T_j	Max Operating Junction Temperature	150	°C



Quality Semi-Conductors

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THERMAL DATA

$R_{thj-case}$	Thermal Resistance Junction-case	Max	1.17	$^{\circ}\text{C/W}$
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ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CER}	Collector Cut-off Current ($R_{BE} = 10\Omega$)	$V_{CE} = V_{CEV}$ $V_{CE} = V_{CEV} \quad T_c = 100^{\circ}\text{C}$			1.5	mA
I_{CEV}	Collector Cut-off Current	$V_{CE} = V_{CEV} \quad V_{BE} = -1.5\text{V}$ $V_{CE} = V_{CEV} \quad V_{BE} = -1.5\text{V} \quad T_c = 100^{\circ}\text{C}$			1.5	mA
I_{EBO}	Emitter Cut-off Current ($I_C = 0$)	$V_{EB} = 5\text{V}$			1	mA
$V_{CEO(sus)*}$	Collector-Emitter Sustaining Voltage	$I_C = 0.2\text{A}$ $L = 25\text{ mH}$	125			V
V_{EBO}	Emitter-base Voltage ($I_C = 0$)	$I_E = 50\text{ mA}$	7			V
$V_{CE(sat)*}$	Collector-Emitter Saturation Voltage	$I_C = 10\text{A} \quad I_B = 0.5\text{A}$		0.4	0.8	V
		$I_C = 20\text{A} \quad I_B = 2\text{A}$		0.6	0.9	V
		$I_C = 24\text{A} \quad I_B = 3\text{A}$		0.7	1.2	V
		$I_C = 10\text{A} \quad I_B = 0.5\text{A} \quad T_j = 100^{\circ}\text{C}$		0.5	0.9	V
		$I_C = 20\text{A} \quad I_B = 2\text{A} \quad T_j = 100^{\circ}\text{C}$		0.75	1.5	V
		$I_C = 24\text{A} \quad I_B = 3\text{A} \quad T_j = 100^{\circ}\text{C}$		0.9	1.8	V
$V_{BE(sat)*}$	Base-Emitter Saturation Voltage	$I_C = 20\text{A} \quad I_B = 2\text{A}$		1.25	1.6	V
		$I_C = 24\text{A} \quad I_B = 3\text{A}$		1.35	1.7	V
		$I_C = 20\text{A} \quad I_B = 2\text{A} \quad T_j = 100^{\circ}\text{C}$		1.25	1.7	V
		$I_C = 24\text{A} \quad I_B = 3\text{A} \quad T_j = 100^{\circ}\text{C}$		1.45	1.9	V
$dI_C/dt*$	Rate of Rise of on-state Collector Current	$V_{CC} = 100\text{V} \quad I_{B1} = 3\text{A}$ $R_C = 0$ $T_j = 25^{\circ}\text{C}$ $T_j = 100^{\circ}\text{C}$	50 45	100 85		A/ μs A/ μs
$V_{CE(2\mu\text{s})}$	Collector-Emitter Dynamic Voltage	$V_{CC} = 100\text{V} \quad I_{B1} = 2\text{A}$ $R_C = 5\Omega$ $T_j = 25^{\circ}\text{C}$ $T_j = 100^{\circ}\text{C}$		1.4 2.1	3 4	V V
$V_{CE(4\mu\text{s})}$	Collector-Emitter Dynamic Voltage	$V_{CC} = 100\text{V} \quad I_{B1} = 2\text{A}$ $R_C = 5\Omega$ $T_j = 25^{\circ}\text{C}$ $T_j = 100^{\circ}\text{C}$		1.1 1.5	2 2.5	V V

* Pulsed: Pulse duration = 300 μs , duty cycle = 2 %

ELECTRICAL CHARACTERISTICS (continued)

TURN-OFF SWITCHING CHARACTERISTICS
On Inductive Load (with negative bias)

Symbol	Test Conditions			Min.	Typ.	Max.	Unit
t_{si}	$T_j = 25^\circ C$	$I_C = 20A \quad I_B = 2A \quad V_{BB} = -5V$	$V_{CC} = 100V \quad V_{CLAMP} = 125V$		0.85	1.4	μs
	$T_j = 100^\circ C$				1.2	1.7	
t_{ri}	$T_j = 25^\circ C$	$I_C = 20A \quad I_B = 2A \quad V_{BB} = -5V$	$V_{CC} = 100V \quad V_{CLAMP} = 125V$		0.09	0.2	μs
	$T_j = 100^\circ C$				0.17	0.3	
t_{ti}	$T_j = 25^\circ C$	$I_C = 0.25 mH \quad R_{B2} = 1.3\Omega$	$R_{B2} = 1.3\Omega$		0.04	0.05	μs
	$T_j = 100^\circ C$				0.07	0.1	
t_c	$T_j = 25^\circ C$				0.16	0.3	μs
	$T_j = 100^\circ C$				0.3	0.5	

TURN-OFF SWITCHING CHARACTERISTICS
On Inductive Load (without negative bias)

Symbol	Test Conditions			Min.	Typ.	Max.	Unit
t_{si}	$T_j = 25^\circ C$	$I_C = 20A \quad I_B = 2A \quad V_{BB} = 0$	$V_{CC} = 100V \quad V_{CLAMP} = 125V$		2.1		μs
	$T_j = 100^\circ C$				3.2		
t_{ri}	$T_j = 25^\circ C$	$I_C = 0.25 mH \quad R_{B2} = 4.7\Omega$	$R_{B2} = 4.7\Omega$		0.7		μs
	$T_j = 100^\circ C$				1.2		
t_{ti}	$T_j = 25^\circ C$				0.28		μs
	$T_j = 100^\circ C$				0.55		

*Pulsed : Duration = 300ms, Duty Cycle = 2 %

Figure 1 : Switching Times Test Circuit (resistive load)

